

# 2SD2606

Silicon NPN diffusion planar type Darlington

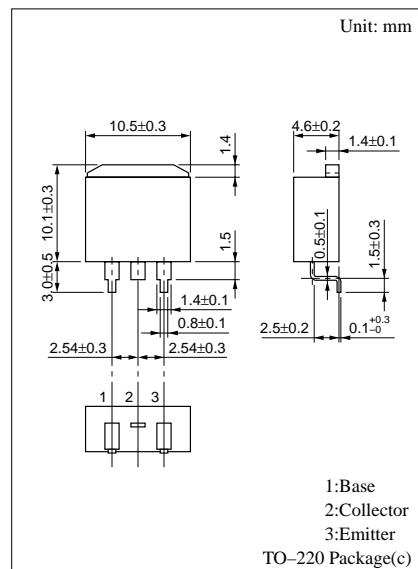
For power amplification

## ■ Features

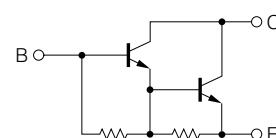
- Extremely satisfactory linearity of the forward current transfer ratio  $h_{FE}$
- High collector to base voltage  $V_{CBO}$
- Wide area of safe operation (ASO)
- TO-220(c) type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

## ■ Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	500	V
Collector to emitter voltage	$V_{CEO}$	400	V
Emitter to base voltage	$V_{EBO}$	12	V
Peak collector current	$I_{CP}$	14	A
Collector current	$I_C$	7	A
Collector power dissipation	$P_C$	50	W
		1.4	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



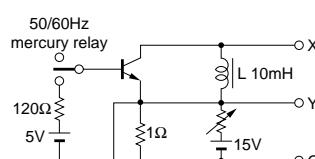
## Internal Connection

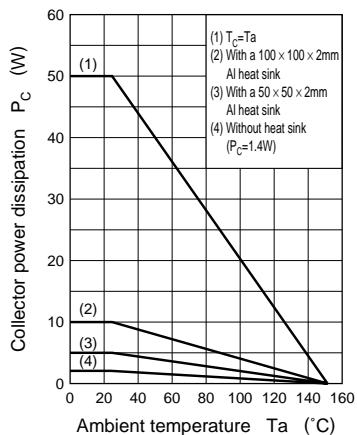


## ■ Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 500\text{V}, I_E = 0$			100	$\mu\text{A}$
	$I_{CEO}$	$V_{CE} = 400\text{V}, I_E = 0$			100	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 12\text{V}, I_C = 0$			100	mA
Collector to emitter voltage	$V_{CEO(sus)}$	$I_C = 100\text{mA}, R_{BE} = \infty$	400			V
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = 2\text{V}, I_C = 2\text{A}$	500			
	$h_{FE2}$	$V_{CE} = 2\text{V}, I_C = 6\text{A}$	200			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 7\text{A}, I_B = 70\text{mA}$			2.0	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 7\text{A}, I_B = 70\text{mA}$			2.5	V
Transition frequency	$f_T$	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}, f = 1\text{MHz}$	20			MHz
Turn-on time	$t_{on}$	$I_C = 7\text{A}, I_{B1} = 70\text{mA}, I_{B2} = -70\text{mA}, V_{CC} = 300\text{V}$		1.5		$\mu\text{s}$
Storage time	$t_{stg}$			5.0		$\mu\text{s}$
Fall time	$t_f$			6.5		$\mu\text{s}$
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		70		pF

\* $V_{CEO(sus)}$  Test circuit



$P_C - Ta$ 

Area of safe operation (ASO)

